

Description

The DMP2123L uses advanced trench technology to provide excellent $R_{DS(ON)}$, low gate charge and operation with gate voltages as low as 2.5V. This device is suitable for use as a load switch or in PWM applications.

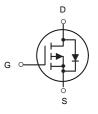


SOT-23

General Features

 $V_{DS} = -20V, I_{D} = -4.2A$

 $R_{DS(ON)}$ < 75m Ω @ V_{GS} =-2.5V



P-Channel MOSFET

Application

PWM applications

Load switch

Power management

Package Marking and Ordering Information

Product ID	Pack	Brand	Qty(PCS)
DMP2123L	SOT-23	HXY MOSFET	3000

Absolute Maximum Ratings (TA=25 ℃ unless otherwise noted)

Symbol	ymbol Parameter		Unit	
V _{DS}	Drain-Source Voltage	-20	V	
V _G S	Gate-Source Voltage	±12	V	
I _D	Drain Current-Continuous	-4.2	А	
Ірм	Drain Current-Pulsed (Note 1)	-15	А	
P _D	Maximum Power Dissipation	1.7	W	
TJ,Tstg	Operating Junction and Storage Temperature Range	-55 To 150	$^{\circ}$	
RеJA	Thermal Resistance,Junction-to-Ambient (Note 2)	74	°C/W	



Electrical Characteristics (T_A=25°C unless otherwise noted)

Parameter	Symbol	Condition	Min	Тур	Max	Unit	
Off Characteristics	•			•			
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V I _D =-250μA	-20	-	-	V	
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =-20V,V _{GS} =0V	-	-	-1	μΑ	
Gate-Body Leakage Current	I _{GSS}	V _{GS} =±12V,V _{DS} =0V	-	-	±100	nA	
On Characteristics (Note 3)							
Gate Threshold Voltage	V _{GS(th)}	V _{DS} =V _{GS} ,I _D =-250μA	-0.45	-0.7	-1.0	V	
Drain Source On State Besistance		V _{GS} =-4.5V, I _D =-4A	-	48	55	mΩ	
Drain-Source On-State Resistance	R _{DS(ON)}	V _{GS} =-2.5V, I _D =-3A	-	60	75		
Forward Transconductance	G FS	V _{DS} =-5V,I _D =-4.2A	-	6	-	S	
Dynamic Characteristics (Note4)			•	•			
Input Capacitance	C _{lss}	V _{DS} =-4V,V _{GS} =0V, F=1.0MHz	-	740	-	PF	
Output Capacitance	C _{oss}		-	290	-	PF	
Reverse Transfer Capacitance	C _{rss}	F-1.UNITZ	-	190	-	PF	
Switching Characteristics (Note 4)							
Turn-on Delay Time	t _{d(on)}		-	12	-	nS	
Turn-on Rise Time	t _r	V_{DD} =-4V, , R_L =-1.2 Ω ,	-	35	-	nS	
Turn-Off Delay Time	$t_{\sf d(off)}$	V_{GEN} =-4.5 V , R_g =1 Ω	-	30	-	nS	
Turn-Off Fall Time	t _f		-	10	-	nS	
Total Gate Charge	Qg		-	7.8	-	nC	
Gate-Source Charge	Q_{gs}	V _{DS} =-4V,I _D =-4.1A,V _{GS} =-4.5V	-	1.2	-	nC	
Gate-Drain Charge	Q_{gd}		-	1.6	-	nC	
Drain-Source Diode Characteristics							
Diode Forward Voltage (Note 3)	V _{SD}	V _{GS} =0V,I _S =-4.1A	-	-	-1.2	V	
Diode Forward Current (Note 2)	Is		-	-	-4.1	Α	

Notes:

- 1. Repetitive Rating: Pulse width limited by maximum junction temperature.
- **2.** Surface Mounted on FR4 Board, $t \le 10$ sec.
- 3. Pulse Test: Pulse Width ≤ 300µs, Duty Cycle ≤ 2%.
- 4. Guaranteed by design, not subject to production



Typical Electrical and Thermal Characteristics

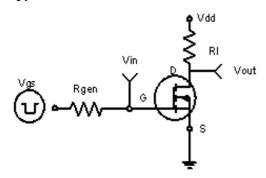


Figure 1:Switching Test Circuit

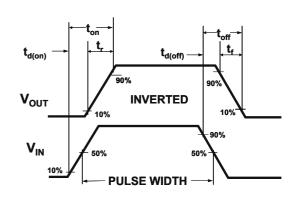


Figure 2:Switching Waveforms

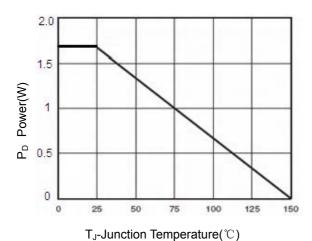


Figure 3 Power Dissipation

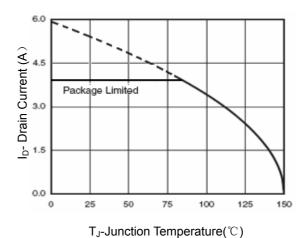


Figure 4 Drain Current

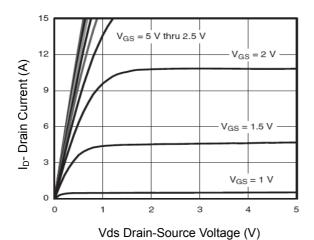


Figure 5 Output Characteristics

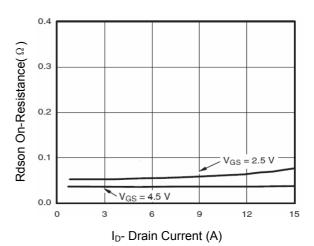


Figure 6 Drain-Source On-Resistance



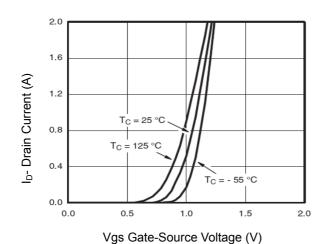


Figure 7 Transfer Characteristics

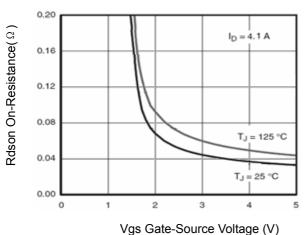


Figure 9 Rdson vs Vgs

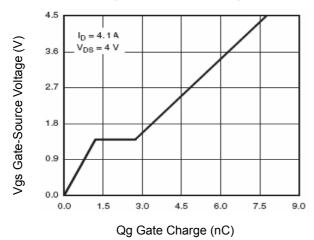


Figure 11 Gate Charge

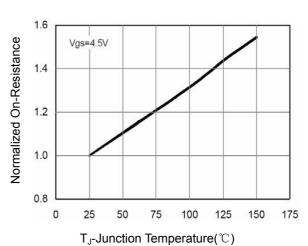


Figure 8 Drain-Source On-Resistance

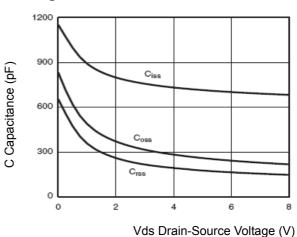
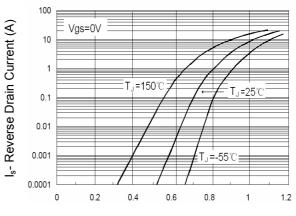
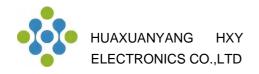


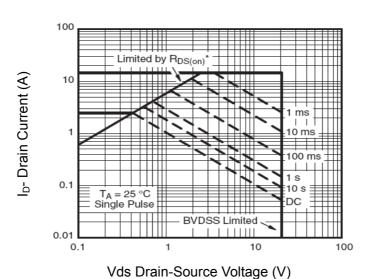
Figure 10 Capacitance vs Vds



Vsd Source-Drain Voltage (V)

Figure 12 Source- Drain Diode Forward





vus Dialii-Source voltage (v)

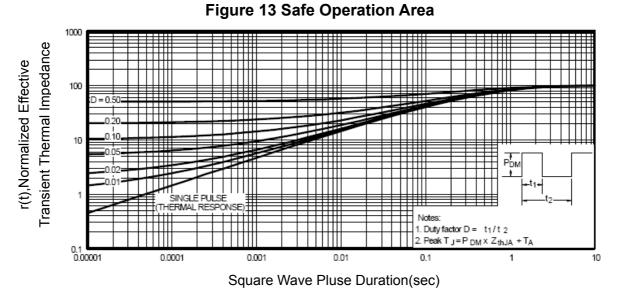
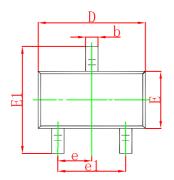
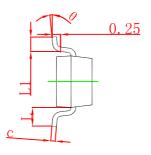


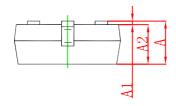
Figure 14 Normalized Maximum Transient Thermal Impedance



SOT-23 Package Outline Dimensions

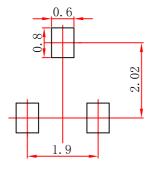






Symbol	Dimensions In Millimeters		Dimensions In Inches		
	Min	Max	Min	Max	
Α	0.900	1.150	0.035	0.045	
A1	0.000	0.100	0.000	0.004	
A2	0.900	1.050	0.035	0.041	
b	0.300	0.500	0.012	0.020	
С	0.080	0.150	0.003	0.006	
D	2.800	3.000	0.110	0.118	
E	1.200	1.400	0.047	0.055	
E1	2.250	2.550	0.089	0.100	
е	0.950	TYP	0.037 TYP		
e1	1.800	2.000	0.071	0.079	
L	0.550 REF		0.022 REF		
L1	0.300	0.500	0.012	0.020	
θ	0°	8°	0°	8°	

SOT-23 Suggested Pad Layout



- Note:
 1.Controlling dimension:in millimeters.
- 2.General tolerance:± 0.05mm.
 3.The pad layout is for reference purposes only.



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